

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CR6AF1GPP SERIES

GLASS PASSIVATED JUNCTION
FAST RECOVERY SILICON RECTIFIER
6.0 AMP, 100 THRU 1000 VOLTS

CASE 106

FEATURES:

- 6 Amps at $T_A = 60^\circ\text{C}$, 3/8" Lead Length
- Glass Passivated Chip
- Compression Molded Epoxy
- Superior Solvent Resistance
- 300 Amps Surge Current
- Reliable Internal Construction
- Extensive Temperature Range

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CR6AF1GPP Series types are 6.0 Amp Glass Passivated Junction Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for use in all types of military, commercial, industrial, entertainment, computer, and automotive applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

MAXIMUM RATINGS: ($T_A = 25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CR6AF1 GPP	CR6AF2 GPP	CR6AF4 GPP	CR6AF6 GPP	CR6AF8 GPP	CR6AF10 GPP	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current @ $T_A = 60^\circ\text{C}$	I_O				6.0			A
Peak Forward Surge Current	I_{FSM}				300			A
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +175			$^\circ\text{C}$

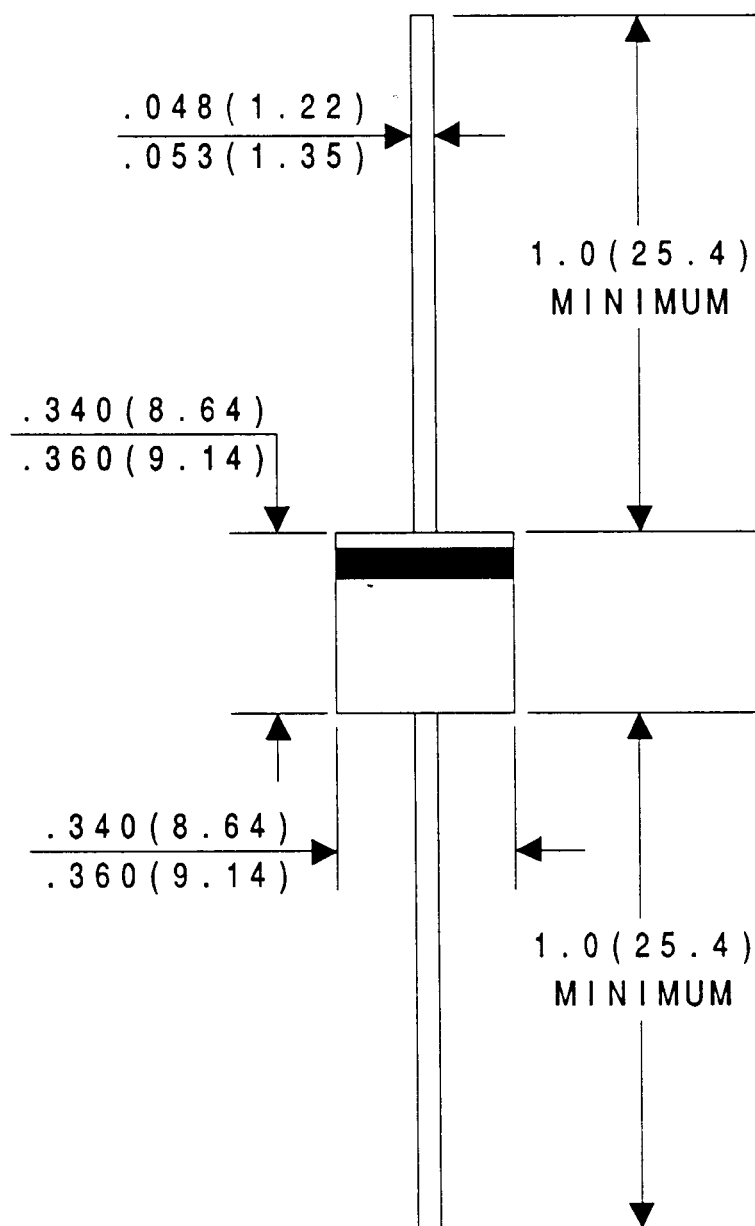
ELECTRICAL CHARACTERISTICS: ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_F	$I_F = 6.0\text{A}$		1.3	V
I_R	$V_R = \text{Rated } V_{RRM}$		10	μA
t_{rr}	$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{rr} = 0.25\text{A}$ (100V thru 400V)		200	ns
t_{rr}	$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{rr} = 0.25\text{A}$ (600V)		250	ns
t_{rr}	$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{rr} = 0.25\text{A}$ (800V thru 1000V)		500	ns

(SEE REVERSE FOR MECHANICAL OUTLINE)



CASE 106 - MECHANICAL OUTLINE



All Dimensions in Inches (mm).